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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0035			
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0040			
I _D (A)	120			
Configuration	Single			
Package	TO-220			

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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N-Channel MOSFET S

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	60	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current	T _C = 25 °C ^a		120		
Continuous drain current	T _C = 125 °C	I _D	102		
Continuous source current (diode conduction) a		I _S	120	Α	
Pulsed drain current ^b		I _{DM}	480		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	100		
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	500	mJ	
Maximum power dissipation ^b	T _C = 25 °C	P _D	250	W	
	T _C = 125 °C		83		
Operating junction and storage temperature ra	ange	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	R_{thJA}	40	°C/W	
Junction-to-case (drain)		R _{thJC}	0.6	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5		
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	900		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0025	0.0035		
During and the second and the second		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0064	Ω	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0080		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0028	0.0040		
Forward transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	190	-	S	
Dynamic ^b	-	-						
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	11 755	14 700	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	1112	1400		
Reverse transfer capacitance	C _{rss}			-	481	605		
Total gate charge ^c	Qg			-	220	330		
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	V _{GS} = 10 V V _{DS} = 30 V, I _D = 110 A		35	-	nC	
Gate-drain charge ^c	Q _{gd}			-	35	-		
Gate resistance	R _g	f = 1 MHz		0.6	1.3	2	Ω	
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 30 \text{ V}, \text{ R}_L = 0.27 \Omega$ $I_D \cong 110 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 2.5 \Omega$		-	19	29	ns ns	
Rise time ^c	t _r			-	23	35		
Turn-off delay time ^c	t _{d(off)}			-	83	125		
Fall time ^c	t _f			-	35	53		
Source-Drain Diode Ratings and Char	racteristics ^b	<u>, </u>						
Pulsed current ^a	I _{SM}			-	-	480	Α	
Forward voltage	V _{SD}	$I_F = 50 \text{ A}, V_{GS} = 0$		-	0.8	1.5	V	
	•			•		•	•	

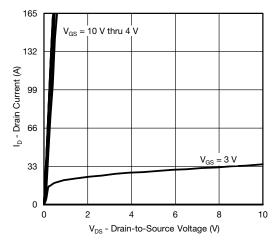
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

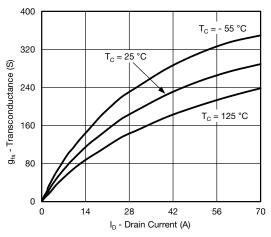
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



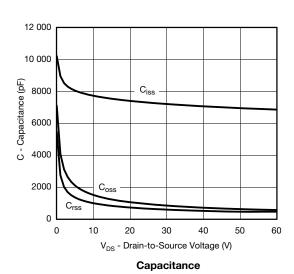
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

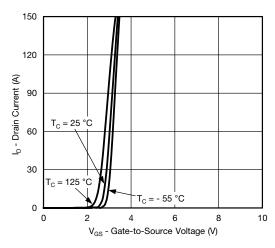


Output Characteristics

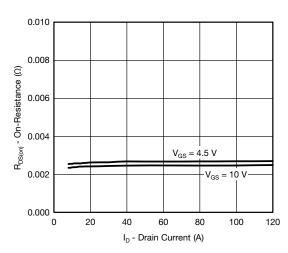


Transconductance

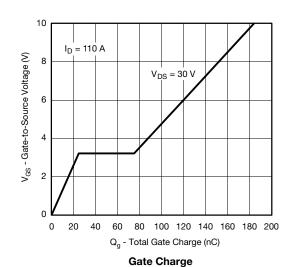




Transfer Characteristics

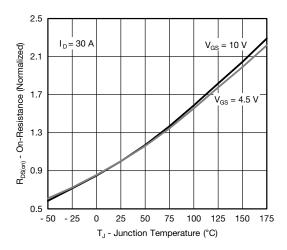


On-Resistance vs. Drain Current

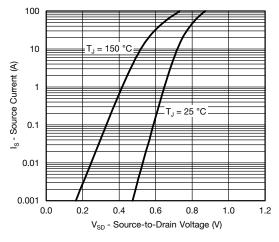




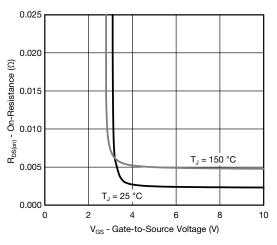
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



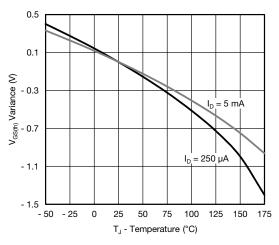
On-Resistance vs. Junction Temperature



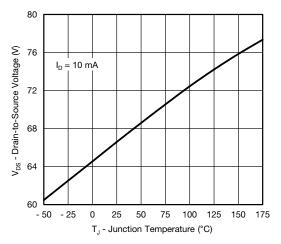
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



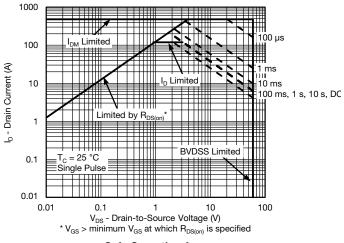
Threshold Voltage



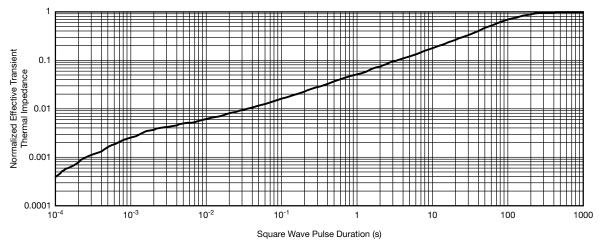
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



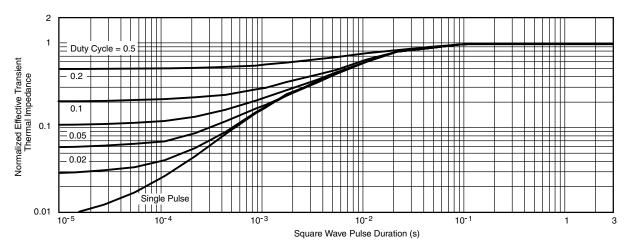
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262854.



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TO-220

Ordering codes for the SQ rugged series power MOSFETs in the TO-220 package:

DATASHEET PART NUMBER	OLD ORDERING CODE a	NEW ORDERING CODE
SQP100N04-3m6	-	SQP100N04-3M6_GE3
SQP100P06-9m3L	-	SQP100P06-9M3L_GE3
SQP120N06-06	-	SQP120N06-06_GE3
SQP120N06-3m5L	SQP120N06-3M5L-GE3	SQP120N06-3M5L_GE3
SQP120N10-09	SQP120N10-09-GE3	SQP120N10-09_GE3
SQP120N10-3m8	SQP120N10-3M8-GE3	SQP120N10-3M8_GE3
SQP25N15-52	-	SQP25N15-52_GE3
SQP50N06-09L	SQP50N06-09L-GE3	SQP50N06-09L_GE3
SQP50P03-07	SQP50P03-07-GE3	SQP50P03-07_GE3
SQP60N06-15	SQP60N06-15-GE3	SQP60N06-15_GE3
SQP90P06-07L	SQP90P06-07L-GE3	SQP90P06-07L_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders



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